IMPROVED BODY CONTACT FET

ABSTRACT

A field-effect transistor (FET) and a radio-frequency module are provided comprising an active region comprising a source region, a drain region, a body region disposed between the source region and the drain region, a first body extension portion in contact with the body region, a second body extension portion in contact with the body region, and a body contact region in contact with the first extension portion and the second extension portion; and a gate disposed on a top surface of the body region. A die is also provided comprising two or more such FETs.

[FIG. 2B]